





CC1120 High-Performance RF Transceiver for Narrowband Systems

1 Device Overview

1.1 Features

- · High-Performance, Single-Chip Transceiver
 - Adjacent Channel Selectivity: 64 dB at 12.5-kHz Offset
 - Blocking Performance: 91 dB at 10 MHz
 - Excellent Receiver Sensitivity:
 - -123 dBm at 1.2 kbps
 - –110 dBm at 50 kbps
 - -127 dBm Using Built-in Coding Gain
 - Very Low Phase Noise: –111 dBc/Hz at 10-kHz Offset
- Suitable for Systems Targeting ETSI Category 1 Compliance in 169-MHz and 433-MHz Bands
- High Spectral Efficiency (9.6 kbps in 12.5-kHz Channel in Compliance With FCC Narrowbanding Mandate)
- · Separate 128-Byte RX and TX FIFOs
- Support for Seamless Integration With the CC1190 Device for Increased Range Giving up to 3-dB Improvement in Sensitivity and up to +27-dBm Output Power
- Power Supply
 - Wide Supply Voltage Range (2.0 V to 3.6 V)
 - Low Current Consumption:
 - RX: 2 mA in RX Sniff Mode
 - RX: 17 mA Peak Current in Low-Power Mode
 - RX: 22 mA Peak Current in High-Performance Mode
 - TX: 45 mA at +14 dBm
 - Power Down: 0.12 μA (0.5 μA With eWOR Timer Running)
- Programmable Output Power up to +16 dBm With

1.2 Applications

- Narrowband Ultra-Low-Power Wireless Systems With Channel Spacing Down to 12.5 kHz
- 169-, 315-, 433-, 868-, 915-, 920-, 950-MHz ISM/SRD Band
- Wireless Metering and Wireless Smart Grid (AMR and AMI)

- 0.4-dB Step Size
- Automatic Output Power Ramping
- Configurable Data Rates: 0 to 200 kbps
- Supported Modulation Formats: 2-FSK, 2-GFSK, 4-FSK, 4-GFSK, MSK, OOK
- WaveMatch: Advanced Digital Signal Processing for Improved Sync Detect Performance
- RoHS-Compliant 5-mm x 5-mm No-Lead QFN 32-Pin Package (RHB)
- Regulations Suitable for Systems Targeting Compliance With
 - Europe: ETSI EN 300 220, ETSI EN 54-25
 - US: FCC CFR47 Part 15, FCC CFR47 Part 90, 24, and 101
 - Japan: ARIB RCR STD-T30, ARIB STD-T67, ARIB STD-T108
- Peripherals and Support Functions
 - Enhanced Wake-On-Radio (eWOR)
 Functionality for Automatic Low-Power Receive Polling
 - Includes Functions for Antenna Diversity Support
 - Support for Retransmissions
 - Support for Auto-Acknowledge of Received Packets
 - TCXO Support and Control, also in Power Modes
 - Automatic Clear Channel Assessment (CCA) for Listen-Before-Talk (LBT) Systems
 - Built-in Coding Gain Support for Increased Range and Robustness
 - Digital RSSI Measurement
 - Temperature Sensor
- IEEE 802.15.4g Systems
- Home and Building Automation
- Wireless Alarm and Security Systems
- Industrial Monitoring and Control
- Wireless Healthcare Applications
- Wireless Sensor Networks and Active RFID
- Private Mobile Radios





1.3 Description

The CC1120 device is a fully integrated single-chip radio transceiver designed for high performance at very low-power and low-voltage operation in cost-effective wireless systems. All filters are integrated, thus removing the need for costly external SAW and IF filters. The device is mainly intended for the ISM (Industrial, Scientific, and Medical) and SRD (Short Range Device) frequency bands at 164–192 MHz, 274–320 MHz, 410–480 MHz, and 820–960 MHz.

The CC1120 device provides extensive hardware support for packet handling, data buffering, burst transmissions, clear channel assessment, link quality indication, and Wake-On-Radio. The main operating parameters of the CC1120 device can be controlled through an SPI interface. In a typical system, the CC1120 device will be used with a microcontroller and only a few external passive components.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE
CC1120RHB	VQFN (32)	5.00 mm x 5.00 mm

(1) For more information, see Section 8, Mechanical Packaging and Orderable Information

1.4 Functional Block Diagram

Figure 1-1 shows the system block diagram of the CC1120 devices.

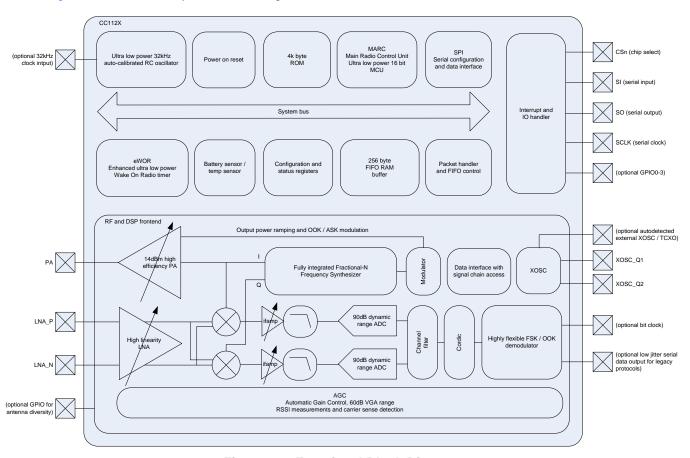


Figure 1-1. Functional Block Diagram



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2 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

This data manual revision history highlights the changes made to the SWRS112F device-specific data manual to make it an SWRS112G revision.

Chan	ges from Revision F (July 2014) to Revision G	Page
•	Added Ambient to the temperature range condition and removed Tj from Temperature range	<u>7</u>
•	Added data to TCXO table	<u>18</u>



3 Terminal Configuration and Functions

3.1 Pin Diagram

Figure 3-1 shows pin names and locations for the CC1120 device.

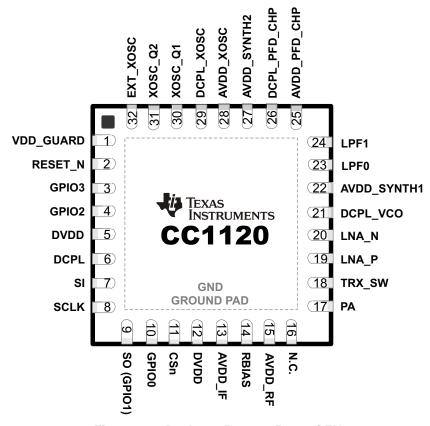


Figure 3-1. Package 5-mm × 5-mm QFN



3.2 Pin Configuration

The following table lists the pinout configuration for the CC1120 device.

PIN NO.	PIN NAME	TYPE / DIRECTION	DESCRIPTION		
1	VDD_GUARD	Power	2.0-3.6 V VDD		
2	RESET_N	Digital input	Asynchronous, active-low digital reset		
3	GPIO3	Digital I/O	General-purpose I/O		
4	GPIO2	Digital I/O	General-purpose I/O		
5	DVDD	Power	2.0–3.6 VDD to internal digital regulator		
6	DCPL	Power	Digital regulator output to external decoupling capacitor		
7	SI	Digital input	Serial data in		
8	SCLK	Digital input	Serial data clock		
9	SO(GPIO1)	Digital I/O	Serial data out (general-purpose I/O)		
10	GPIO0	Digital I/O	General-purpose I/O		
11	CSn	Digital input	Active-low chip select		
12	DVDD	Power	2.0-3.6 V VDD		
13	AVDD_IF	Power	2.0-3.6 V VDD		
14	RBIAS	Analog	External high-precision resistor		
15	AVDD_RF	Power	2.0–3.6 V VDD		
16	N.C.		Not connected		
17	PA	Analog	Single-ended TX output (requires DC path to VDD)		
18	TRX_SW	Analog	TX and RX switch. Connected internally to GND in TX and floating (high-impedance) in RX.		
19	LNA_P	Analog	Differential RX input (requires DC path to ground)		
20	LNA_N	Analog	Differential RX input (requires DC path to ground)		
21	DCPL_VCO	Power	Pin for external decoupling of VCO supply regulator		
22	AVDD_SYNTH1	Power	2.0-3.6 V VDD		
23	LPF0	Analog	External loop filter components		
24	LPF1	Analog	External loop filter components		
25	AVDD_PFD_CHP	Power	2.0-3.6 V VDD		
26	DCPL_PFD_CHP	Power	Pin for external decoupling of PFD and CHP regulator		
27	AVDD_SYNTH2	Power	2.0-3.6 V VDD		
28	AVDD_XOSC	Power	2.0–3.6 V VDD		
29	DCPL_XOSC	Power	Pin for external decoupling of XOSC supply regulator		
30	XOSC_Q1	Analog	Crystal oscillator pin 1 (must be grounded if a TCXO or other external clock connected to EXT_XOSC is used)		
31	XOSC_Q2	Analog	Crystal oscillator pin 2 (must be left floating if a TCXO or other external clock connected to EXT_XOSC is used)		
32	EXT_XOSC	Digital input	Pin for external clock input (must be grounded if regular crystal connected to XOSC_Q1 and XOSC_Q2 is used)		
_	GND	Ground pad	The ground pad must be connected to a solid ground plane.		



4 Specifications

All measurements performed on CC1120EM_868_915 rev.1.0.1, CC1120EM_955 rev.1.2.1, CC1120EM_420_470 rev.1.0.1, or CC1120EM_169 rev.1.2.

4.1 Absolute Maximum Ratings (1)(2)

PARAMETER	MIN	MAX	UNIT	CONDITION
Supply voltage (VDD, AVDD_x)	-0.3	3.9	٧	All supply pins must have the same voltage
Input RF level		+10	dBm	
Voltage on any digital pin	-0.3	VDD+0.3	٧	max 3.9 V
Voltage on analog pins (including DCPL pins)	-0.3	2.0	٧	

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under general characteristics is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

4.2 Handling Ratings

				MIN	MAX	UNIT
T _{stg}	Storage temperature	erature range				°C
	Electrostatic	Human body model (HBM), per ANSI/ESDA/JEDEC JS00	1 ⁽¹⁾	-2	2	kV
V _{ESD}	discharge (ESD) performance:	Charged device model (CDM), per JESD22-C101 (2)	All pins	-500	500	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

4.3 Recommended Operating Conditions (General Characteristics)

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
Voltage supply range	2.0		3.6	V	All supply pins must have the same voltage
Voltage on digital inputs	0		VDD	V	
Temperature range	-40		85	°C	Ambient

4.4 Thermal Resistance Characteristics for RHB Package

		°C/W ⁽¹⁾	AIR FLOW (m/s) ⁽²⁾
$R\theta_{JC}$	Junction-to-case (top)	21.1	0.00
$R\theta_{JB}$	Junction-to-board	5.3	0.00
$R\theta_{JA}$	Junction-to-free air	31.3	0.00
Psi _{JT}	Junction-to-package top	0.2	0.00
Psi _{JB}	Junction-to-board	5.3	0.00
$R\theta_{JC}$	Junction-to-case (bottom)	0.8	0.00

⁽¹⁾ These values are based on a JEDEC-defined 2S2P system (with the exception of the Theta JC [RΘ_{JC}] value, which is based on a JEDEC-defined 1S0P system) and will change based on environment as well as application. For more information, see these EIA/JEDEC standards:

(2) m/s = meters per second

All voltage values are with respect to V_{SS}, unless otherwise noted.

⁽²⁾ JEDEC document JEP157 states that 250-V HBM allows safe manufacturing with a standard ESD control process.

JESD51-2, Integrated Circuits Thermal Test Method Environmental Conditions - Natural Convection (Still Air)

JESD51-3, Low Effective Thermal Conductivity Test Board for Leaded Surface Mount Packages

[•] JESD51-7, High Effective Thermal Conductivity Test Board for Leaded Surface Mount Packages

JESD51-9, Test Boards for Area Array Surface Mount Package Thermal Measurements

Power dissipation of 40 mW and an ambient temperature of 25°C is assumed.



4.5 RF Characteristics

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
	820		960	MHz	
	410		480	MHz	
Frequency bands	(273.3)		(320)	MHz	See SWRA398, Using the CC112x/CC1175 at 274 to 320 MHz, for more information
	164		192	MHz	
	(205)		(240)	MHz	Contact TI for more
	(136.7)		(160)	MHz	information about the use of these frequency bands.
		30		Hz	In 820–950 MHz band
Frequency resolution		15		Hz	In 410–480 MHz band
		6		Hz	In 164–192 MHz band
Data sala	0		200	kbps	Packet mode
Data rate	0		100	kbps	Transparent mode
Data rate step size		1e-4		bps	



4.6 Regulatory Standards

PERFORMANCE MODE	FREQUENCY BAND	SUITABLE FOR COMPLIANCE WITH	COMMENTS
	820–960 MHz	ARIB T-96 ARIB T-108 ETSI EN 300 220 category 2 ETSI EN 54-25 FCC PART 101 FCC PART 24 SUBMASK D FCC PART 15.247 FCC PART 15.249 FCC PART 90 MASK G FCC PART 90 MASK J	Performance also suitable for systems targeting maximum allowed output power in the respective bands, using a range extender such as the CC1190 device
High-performance mode	410–480 MHz	ARIB T-67 ARIB RCR STD-30 ETSI EN 300 220 category 1 FCC PART 90 MASK D FCC PART 90 MASK G	Performance also suitable for systems targeting maximum allowed output power in the respective bands, using a range extender
	164–192 MHz	ETSI EN 300 220 category 1 FCC PART 90 MASK D	Performance also suitable for systems targeting maximum allowed output power in the respective bands, using a range extender
Low-power mode	820–960 MHz	ETSI EN 300 220 category 2 FCC PART 15.247 FCC PART 15.249	
	410–480 MHz	ETSI EN 300 220 category 2	
	164–192 MHz	ETSI EN 300 220 category 2	

4.7 Current Consumption, Static Modes

 $T_A = 25$ °C, VDD = 3.0 V if nothing else stated

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
Down down with retention		0.12	1	μA	
Power down with retention		0.5		μA	Low-power RC oscillator running
XOFF mode		170		μA	Crystal oscillator / TCXO disabled
IDLE mode		1.3		mA	Clock running, system waiting with no radio activity



Current Consumption, Transmit Modes

4.8.1 950-MHz Band (High-Performance Mode)

 $T_A = 25$ °C, VDD = 3.0 V if nothing else stated

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
TX current consumption +10 dBm		37		mA	
TX current consumption 0 dBm		26		mA	

4.8.2 868-, 915-, and 920-MHz Bands (High-Performance Mode)

 $T_A = 25$ °C, VDD = 3.0 V if nothing else stated

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
TX current consumption +14 dBm		45		mA	
TX current consumption +10 dBm		34		mA	

4.8.3 434-MHz Band (High-Performance Mode)

 $T_A = 25$ °C, VDD = 3.0 V if nothing else stated

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
TX current consumption +15 dBm		50		mA	
TX current consumption +14 dBm		45		mA	
TX current consumption +10 dBm		34		mA	

4.8.4 169-MHz Band (High-Performance Mode)

 $T_A = 25^{\circ}C$. VDD = 3.0 V if nothing else stated

PARAMETER		TYP	MAY	LINUT	CONDITION
PARAMETER	MIN	ITP	MAX	UNIT	CONDITION
TX current consumption +15 dBm		54		mA	
TX current consumption +14 dBm		49		mA	
TX current consumption +10 dBm		41		mA	

4.8.5 Low-Power Mode

 $T_A = 25$ °C, VDD = 3.0 V, $f_c = 869.5$ MHz if nothing else stated

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
TX current consumption +10 dBm		32		mA	

10



4.9 Current Consumption, Receive Modes

4.9.1 High-Performance Mode

 $T_A = 25$ °C, VDD = 3.0 V, $f_c = 869.5$ MHz if nothing else stated

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
RX Wait for sync					Using RX sniff mode, where the receiver wakes up at regular
1.2 kbps, 4-byte preamble		2		mA	intervals to look for an incoming
38.4 kbps, 4-byte preamble		13.4		mA	packet
RX Peak Current					Peak current consumption during
433-, 868-, 915-, 920-, and 950-MHz bands		22		mA	packet reception at the sensitivity
169-MHz band		23		mA	threshold
Average current consumption Check for data packet every 1 second using Wake on Radio		15		μΑ	50 kbps, 5-byte preamble, 40-kHz RC oscillator used as sleep timer

4.9.2 Low-Power Mode

 $T_A = 25$ °C, VDD = 3.0 V, $f_c = 869.5$ MHz if nothing else stated

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
RX Peak Current Low-power RX mode					Peak current consumption during
1.2 kbps		17		mA	packet reception at the sensitivity level

4.10 Receive Parameters

All RX measurements made at the antenna connector, to a bit error rate (BER) limit of 1%.

4.10.1 General Receive Parameters (High-Performance Mode)

 $T_A = 25$ °C. VDD = 3.0 V. $f_A = 869.5$ MHz if nothing else stated

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
Saturation		+10		dBm	
Digital Channel Filter Programmable Bandwidth	8		200	kHz	
IIP3, Normal mode		-14		dBm	At maximum gain
IIP3, High Linearity mode		-8		dBm	Using 6 dB gain reduction in front end
Datarate Offset Tolerance		±12		%	With carrier sense detection enabled and assuming 4 byte preamble
		±0.2		%	With carrier sense detection disabled
Spurious Emissions					Radiated emissions measured
1-13 GHz (VCO leakage at 3.5 GHz)		- 56		dBm	according to ETSI EN 300 220,
30 MHz to 1 GHz		< -57		dBm	fc = 869.5 MHz
Optimum Source Impedance					
868-, 915-, and 920-MHz bands	60) + j60 / 30+j	30	Ω	(Differential or Single-Ended RX
433-MHz band	10	0 + j60 / 50+	j30	Ω	Configurations)
169-MHz band	140) + j40 / 70 +	j20	Ω	



4.10.2 RX Performance in 950-MHz Band (High-Performance Mode)

 $T_{\Delta} = 25^{\circ}C$, VDD = 3.0 V if nothing else stated

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
		-120		dBm	1.2 kbps, DEV=4 kHz CHF=10 kHz ⁽¹⁾
o		-114		dBm	1.2 kbps, DEV=20 kHz CHF=50 kHz ⁽¹⁾
Sensitivity Note: Sensitivity can be improved if the TX and RX matching networks are separated.		-107		dBm	50 kbps 2GFSK, DEV=25 kHz, CHF=100 kHz ⁽¹⁾
		-100		dBm	200 kbps, DEV=83 kHz (outer symbols), CHF=200 kHz ⁽¹⁾ , 4GFSK ⁽²⁾
		51		dB	± 12.5 kHz (adjacent channel)
Blocking and Selectivity		52		dB	± 25 kHz (alternate channel)
1.2 kbps 2FSK, 12.5-kHz channel separation,		73		dB	± 1 MHz
4-kHz deviation, 10-kHz channel filter		76		dB	± 2 MHz
		81		dB	± 10 MHz
		47		dB	± 50 kHz (adjacent channel)
Blocking and Selectivity		48		dB	+ 100 kHz (alternate channel)
1.2 kbps 2FSK, 50-kHz channel separation,		69		dB	± 1 MHz
20-kHz deviation, 50-kHz channel filter		71		dB	± 2 MHz
		78		dB	± 10 MHz
		43		dB	± 200 kHz (adjacent channel)
Blocking and Selectivity 50 kbps 2GFSK, 200-kHz channel separation,		51		dB	± 400 kHz (alternate channel)
25-kHz deviation, 100-kHz channel filter		62		dB	± 1 MHz
(Same modulation format as 802.15.4g Mandatory Mode)		65		dB	± 2 MHz
Walidatory Wode)		71		dB	± 10 MHz
		37		dB	± 200 kHz (adjacent channel)
Blocking and Selectivity		44		dB	± 400 kHz (alternate channel)
200 kbps 4GFSK, 83-kHz deviation (outer		55		dB	± 1 MHz
symbols), 200-kHz channel filter, zero IF		58		dB	± 2 MHz
		64		dB	± 10 MHz

⁽¹⁾ DEV is short for deviation, CHF is short for Channel Filter Bandwidth

⁽²⁾ BT=0.5 is used in all GFSK measurements



4.10.3 RX Performance in 868-, 915-, and 920-MHz Bands (High-Performance Mode)

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
		-127		dBm	300 bps with coding gain (using a PN spreading sequence with 4 chips per databit) DEV=4 kHz CHF=10 kHz ⁽¹⁾
		-123		dBm	1.2 kbps, DEV=4 kHz CHF=10 kHz ⁽¹⁾
		-120		dBm	1.2 kbps, DEV=10 kHz CHF=42 kHz ⁽¹⁾
Consisting to		-117		dBm	1.2 kbps, DEV=20 kHz CHF=50 kHz ⁽¹⁾
Sensitivity		-114		dBm	4.8 kbps OOK
		-110		dBm	38.4 kbps, DEV=20 kHz CHF=100 kHz ⁽¹⁾
		-110		dBm	50 kbps 2GFSK, DEV=25 kHz, CHF=100 kHz ⁽¹⁾
		-103		dBm	200 kbps, DEV=83 kHz (outer symbols), CHF=200 kHz ⁽¹⁾ , 4GFSK
		54		dB	± 12.5 kHz (adjacent channel)
Blocking and Selectivity		54		dB	± 25 kHz (alternate channel)
1.2-kbps 2-FSK, 12.5-kHz channel separation,		75		dB	± 1 MHz
4-kHz deviation, 10-kHz channel filter		79		dB	± 2 MHz
		87		dB	± 10 MHz
Blocking		78		dB	± 1 kHz
1.2-kbps 2-FSK, 12.5-kHz channel separation, using settings optimized for blocking		82		dB	± 2 kHz
performance		88		dB	± 8 MHz
(3-kHz deviation, 7.8-kHz channel filter, minimum loop bandwidth)		88		dB	± 10 MHz
		48		dB	± 50 kHz (adjacent channel)
Blocking and Selectivity		48		dB	+ 100 kHz (alternate channel)
1.2-kbps 2-FSK, 50-kHz channel separation,		69		dB	± 1 MHz
20-kHz deviation, 50-kHz channel filter		74		dB	± 2 MHz
		81		dB	± 10 MHz
		42		dB	+ 100 kHz (adjacent channel)
Blocking and Selectivity		43		dB	± 200 kHz (alternate channel)
38.4-kbps 2-GFSK, 100-kHz channel separation, 20-kHz deviation, 100-kHz channel		62		dB	± 1 MHz
filter		66		dB	± 2 MHz
		74		dB	± 10 MHz
		43		dB	± 200 kHz (adjacent channel)
Blocking and Selectivity 50-kbps 2-GFSK, 200-kHz channel separation,		50		dB	± 400 kHz (alternate channel)
25-kHz deviation, 100-kHz channel filter		61		dB	± 1 MHz
(Same modulation format as 802.15.4g Mandatory Mode)		65		dB	± 2 MHz
manadary wodo,		74		dB	± 10 MHz
		36		dB	± 200 kHz (adjacent channel)
Blocking and Selectivity		44		dB	± 400 kHz (alternate channel)
200-kbps 4-GFSK, 83-kHz deviation (outer		55		dB	± 1 MHz
symbols), 200-kHz channel filter, zero IF		59		dB	± 2 MHz
		67		dB	± 10 MHz
Image Rejection (Image compensation enabled)		54		dB	1.2 kbps, DEV=4 kHz CHF=10 kHz ⁽¹⁾ , image at -125 kHz

⁽¹⁾ DEV is short for deviation, CHF is short for Channel Filter Bandwidth



4.10.4 RX Performance in 434-MHz Band (High-Performance Mode)

 $T_{\Delta} = 25^{\circ}C$, VDD = 3.0 V if nothing else stated

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
		-123		dBm	1.2 kbps, DEV=4 kHz CHF=10 kHz ⁽¹⁾
Sensitivity		-109		dBm	50 kbps 2GFSK, DEV=25 kHz, CHF=100 kHz
		-116		dBm	1.2 kbps, DEV=20 kHz CHF=50 kHz ⁽¹⁾
		60		dB	± 12.5 kHz (adjacent channel)
Blocking and Selectivity		60		dB	± 25 kHz (alternate channel)
1.2 kbps 2FSK, 12.5-kHz channel separation,		79		dB	± 1 MHz
4-kHz deviation, 10-kHz channel filter		82		dB	± 2 MHz
	91		dB	± 10 MHz	
		54		dB	± 50 kHz (adjacent channel)
Blocking and Selectivity		54		dB	+ 100 kHz (alternate channel)
1.2 kbps 2FSK, 50-kHz channel separation,		74		dB	± 1 MHz
20-kHz deviation, 50-kHz channel filter		78		dB	± 2 MHz
		86		dB	± 10 MHz
		47		dB	+ 100 kHz (adjacent channel)
Blocking and Selectivity		50		dB	± 200 kHz (alternate channel)
38.4 kbps 2GFSK, 100-kHz channel separation,		67		dB	± 1 MHz
20-kHz deviation, 100-kHz channel filter		71		dB	± 2 MHz
		78		dB	± 10 MHz

⁽¹⁾ DEV is short for deviation, CHF is short for Channel Filter Bandwidth

4.10.5 RX Performance in 169-MHz Band (High-Performance Mode)

 $T_{\Delta} = 25^{\circ}C$, VDD = 3.0 V if nothing else stated

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
Constitute		-123		dBm	1.2 kbps, DEV=4 kHz CHF=10 kHz ⁽¹⁾
Sensitivity		-117		dbm	1.2 kbps, DEV=20 kHz CHF=50 kHz ⁽¹⁾
		64		dB	± 12.5 kHz (adjacent channel)
Blocking and Selectivity		66		dB	± 25 kHz (alternate channel)
1.2 kbps 2FSK, 12.5-kHz channel separation,		82		dB	± 1 MHz
4-kHz deviation, 10-kHz channel filter		83		dB	± 2 MHz
		89		dB	± 10 MHz
		60		dB	± 50 kHz (adjacent channel)
Blocking and Selectivity		60		dB	+ 100 kHz (alternate channel)
1.2 kbps 2FSK, 50-kHz channel separation,		76		dB	± 1 MHz
20-kHz deviation, 50-kHz channel filter		77		dB	± 2 MHz
		83		dB	± 10 MHz
Spurious Response Rejection 1.2 kbps 2FSK, 12.5-kHz channel separation, 4-kHz deviation, 10-kHz channel filter		70		dB	
Image Rejection (Image compensation enabled)		66		dB	1.2 kbps, DEV=4 kHz CHF=10 kHz ⁽¹⁾ , image at -125 kHz

⁽¹⁾ DEV is short for deviation, CHF is short for Channel Filter Bandwidth



4.10.6 RX Performance in Low-Power Mode

 $T_{\Delta} = 25^{\circ}\text{C}$, VDD = 3.0 V, $f_{c} = 869.5$ MHz if nothing else stated

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
		-111		dBm	1.2 kbps, DEV=4 kHz CHF=10 kHz ⁽¹⁾
Sensitivity		-99		dBm	38.4 kbps, DEV=50 kHz CHF=100 kHz ⁽¹⁾
Scholivity		-99		dBm	50 kbps 2GFSK, DEV=25 kHz, CHF=100 kHz ⁽¹⁾
		46		dB	± 12.5 kHz (adjacent channel)
Blocking and Selectivity		46		dB	± 25 kHz (alternate channel)
1.2 kbps 2FSK, 12.5-kHz channel separation,		73		dB	± 1 MHz
4-kHz deviation, 10-kHz channel filter		78		dB	± 2 MHz
		79		dB	± 10 MHz
		43		dB	± 50 kHz (adjacent channel)
Blocking and Selectivity		45		dB	+ 100 kHz (alternate channel)
1.2 kbps 2FSK, 50-kHz channel separation,		71		dB	± 1 MHz
20-kHz deviation, 50-kHz channel filter		74		dB	± 2 MHz
		75		dB	± 10 MHz
		37		dB	+ 100 kHz (adjacent channel)
Blocking and Selectivity		43		dB	+ 200 kHz (alternate channel)
38.4 kbps 2GFSK, 100-kHz channel separation,		58		dB	± 1 MHz
20-kHz deviation, 100-kHz channel filter		62		dB	± 2 MHz
		64		dB	+ 10 MHz
		43		dB	+ 200 kHz (adjacent channel)
Blocking and Selectivity 50 kbps 2GFSK, 200-kHz channel separation,		52		dB	+ 400 kHz (alternate channel)
25-kHz deviation, 100-kHz channel filter		60		dB	± 1 MHz
(Same modulation format as 802.15.4g		64		dB	± 2 MHz
Mandatory Mode)		65		dB	± 10 MHz
Saturation		+10		dBm	

⁽¹⁾ DEV is short for deviation, CHF is short for Channel Filter Bandwidth



4.11 Transmit Parameters

 $T_A = 25$ °C, VDD = 3.0 V, $f_c = 869.5$ MHz if nothing else stated

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
		+12		dBm	At 950 MHz
		+14		dBm	At 915- and 920-MHz
		+15		dBm	At 915- and 920-MHz with VDD = 3.6 V
		+15		dBm	At 868 MHz
Max output power		+16		dBm	At 868 MHz with VDD = 3.6 V
		+15		dBm	At 433 MHz
		+16		dBm	At 433 MHz with VDD = 3.6 V
		+15		dBm	At 169 MHz
		+16		dBm	At 169 MHz with VDD = 3.6 V
Min output nouse		-11		dBm	Within fine step size range
Min output power		-40		dBm	Within coarse step size range
Output power step size		0.4		dB	Within fine step size range
		-75		dBc	4-GFSK 9.6 kbps in 12.5-kHz channel, measured in 100-Hz bandwidth at 434 MHz (FCC Part 90 Mask D compliant)
Adjacent channel power		-58		dBc	4-GFSK 9.6 kbps in 12.5-kHz channel, measured in 8.75-kHz bandwidth (ETSI EN 300 220 compliant)
		-61		dBc	2-GFSK 2.4 kbps in 12.5-kHz channel, 1.2-kHz deviation
Spurious emissions (not including harmonics)		<-60		dBm	
Harmonics					
2nd Harm, 169 MHz		-39		dBm	
3rd Harm, 169 MHz		-58		dBm	
2nd Harm, 433 MHz		-56		dBm	Transmission at +14 dBm (or maximum
3rd Harm, 433 MHz		-51		dBm	allowed in applicable band where this is less than +14 dBm) using TI reference design
2nd Harm, 450 MHz		-60		dBm	Emissions measured according to ARIB T-
3rd Harm, 450 MHz		-45		dBm	96 in 950-MHz band, ETSI EN 300-220 in 170-, 433-, and 868-MHz bands and FCC
2nd Harm, 868 MHz		-40		dBm	part 15.247 in 450- and 915-MHz band
3rd Harm, 868 MHz		-42		dBm	Fourth harmonic in 915-MHz band will
2nd Harm, 915 MHz		56		dBuV/m	require extra filtering to meet FCC requirements if transmitting for long intervals
3rd Harm, 915 MHz		52		dBuV/m	(>50-ms periods)
4th Harm, 915 MHz		60		dBuV/m	
2nd Harm, 950 MHz		-58		dBm	
3rd Harm, 950 MHz		-42		dBm	
Optimum load					
Impedance 868-, 915-, and 920-MHz bands		35 + j35		Ω	
433 MHz band		55 + j25		Ω	
169 MHz band		80 + j0		Ω	



4.12 PLL Parameters

4.12.1 High-Performance Mode

 $T_A = 25$ °C, VDD = 3.0 V if nothing else stated

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
		-99		dBc/Hz	± 10 kHz offset
Phase noise in 950-MHz band		-99		dBc/Hz	± 100 kHz offset
		-123		dBc/Hz	± 1 MHz offset
		-99		dBc/Hz	± 10 kHz offset
Phase noise in 868-, 915-, 920-MHz bands		-100		dBc/Hz	± 100 kHz offset
		-122		dBc/Hz	± 1 MHz offset
		-106		dBc/Hz	± 10 kHz offset
Phase noise in 433-MHz band		-107		dBc/Hz	± 100 kHz offset
		-127		dBc/Hz	± 1 MHz offset
		-111		dBc/Hz	± 10 kHz offset
Phase noise in 169-MHz band		-116		dBc/Hz	± 100 kHz offset
		-135		dBc/Hz	± 1 MHz offset

4.12.2 Low-Power Mode

 $T_A = 25$ °C, VDD = 3.0 V, fc = 869.5 MHz if nothing else stated

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
		-90		dBc/Hz	± 10 kHz offset
Phase noise in 950-MHz band		-92		dBc/Hz	± 100 kHz offset
		-124		dBc/Hz	± 1 MHz offset
		-95		dBc/Hz	± 10 kHz offset
Phase noise in 868-, 915-, 920-MHz bands		-95		dBc/Hz	± 100 kHz offset
		-124		dBc/Hz	± 1 MHz offset
		-98		dBc/Hz	± 10 kHz offset
Phase noise in 433-MHz band		-102		dBc/Hz	± 100 kHz offset
		-129		dBc/Hz	± 1 MHz offset
		-106		dBc/Hz	± 10 kHz offset
Phase noise in 169-MHz band		-110		dBc/Hz	± 100 kHz offset
		-136		dBc/Hz	± 1 MHz offset



4.13 Wake-up and Timing

 $T_A = 25$ °C, VDD = 3.0 V, $f_C = 869.5$ MHz if nothing else stated

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
Powerdown to IDLE		0.4		ms	Depends on crystal
IDLE to DV/TV		166		μs	Calibration disabled
IDLE to RX/TX		461		μs	Calibration enabled
RX/TX turnaround		50		μs	
DV/TV to IDI E time		296		μs	Calibrate when leaving RX/TX enabled
RX/TX to IDLE time		0		μs	Calibrate when leaving RX/TX disabled
Frequency synthesizer calibration		391		μs	When using SCAL strobe
Minimum required number of preamble bytes		0.5		bytes	Required for RF front end gain settling only. Digital demodulation does not require preamble for settling
Time from start RX until valid RSSI		4.6		ms	12.5-kHz channels
Including gain settling (function of channel bandwidth. Programmable for trade-off between speed and accuracy)		0.3		ms	200-kHz channels

4.14 32-MHz Crystal Oscillator

 $T_A = 25$ °C, VDD = 3.0 V if nothing else stated

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
Crystal frequency	32		33.6	MHz	It is expected that there be will degraded sensitivity at multiples of XOSC/2 in RX, and an increase in spurious emissions when the RF channel is close to multiples of XOSC in TX. We recommend that the RF channel is kept RX_BW/2 away from XOSC/2 in RX, and that the level of spurious emissions be evaluated if the RF channel is closer than 1 MHz to multiples of XOSC in TX.
Load capacitance (C _L)		10		pF	
ESR			60	Ω	Simulated over operating conditions
Start-up time		0.4		ms	Depends on crystal

4.15 32-MHz Clock Input (TCXO)

 $T_A = 25$ °C, VDD = 3.0 V if nothing else stated

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
Clock frequency	32		33.6	MHz	
TCXO with CMOS output					TCXO with CMOS output directly
High input voltage	1.4		VDD	V	coupled to pin EXT_OSC
Low input voltage	0		0.6	V	
Rise / Fall time			2	ns	
Clipped sine output					TCXO clipped sine output connected
Clock input amplitude (peak-to-peak)	0.8		1.5	V	to pin EXT_OSC through series capacitor



4.16 32-kHz Clock Input

 $T_A = 25$ °C, VDD = 3.0 V if nothing else stated

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
Clock frequency		32		kHz	
32-kHz clock input pin input high voltage	0.8×VDD			V	
32-kHz clock input pin input high voltage			0.2×VDD	٧	

4.17 32-kHz RC Oscillator

 $T_A = 25$ °C, VDD = 3.0 V if nothing else stated

PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
Frequency		32		kHz	After calibration
Frequency accuracy after calibration		±0.1		%	Relative to frequency reference (32-MHz crystal or TCXO)
Initial calibration time		1.6		ms	

4.18 I/O and Reset

 $T_A = 25$ °C, VDD = 3.0 V if nothing else stated

1A - 20 0, VDD - 0.0 V II Holling Ci	oc statea				
PARAMETER	MIN	TYP	MAX	UNIT	CONDITION
Logic input high voltage	0.8×VDD			٧	
Logic input low voltage			0.2×VDD	V	
Logic output high voltage	0.8×VDD			٧	At 4 mA custnut load or load
Logic output low voltage			0.2×VDD	V	At 4-mA output load or less
Power-on reset threshold		1.3		V	Voltage on DVDD pin

4.19 Temperature Sensor

 $T_{\Delta} = 25^{\circ}C$. VDD = 3.0 V if nothing else stated

TA = 25 C, VDD = 5.0 V II Hottilling else stated									
PARAMETER	MIN	TYP	MAX	UNIT	CONDITION				
Temperature sensor range	-40		85	°C					
Temperature coefficient		2.66		mV / °C	Change in sensor output voltage versus change in temperature				
Typical output voltage		794		mV	Typical sensor output voltage at $T_A = 25$ °C, VDD = 3.0 V				
VDD coefficient		1.17		mV / V	Change in sensor output voltage versus change in VDD				

The CC1120 device can be configured to provide a voltage proportional to temperature on GPIO1. The temperature can be estimated by measuring this voltage (See Section 4.19, *Temperature Sensor*). For more information, see the temperature sensor design note (SWRA415).

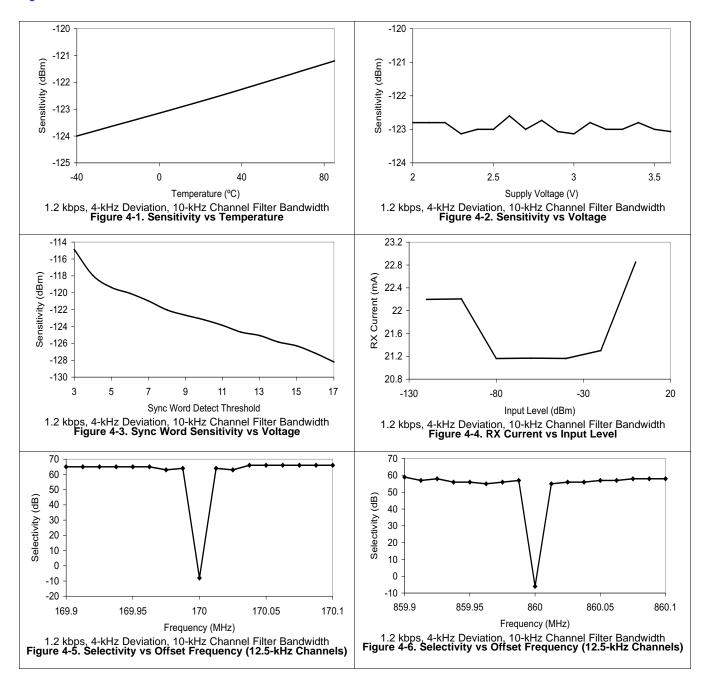


4.20 Typical Characteristics

 $T_A = 25$ °C, VDD = 3.0 V, $f_c = 869.5$ MHz if nothing else stated.

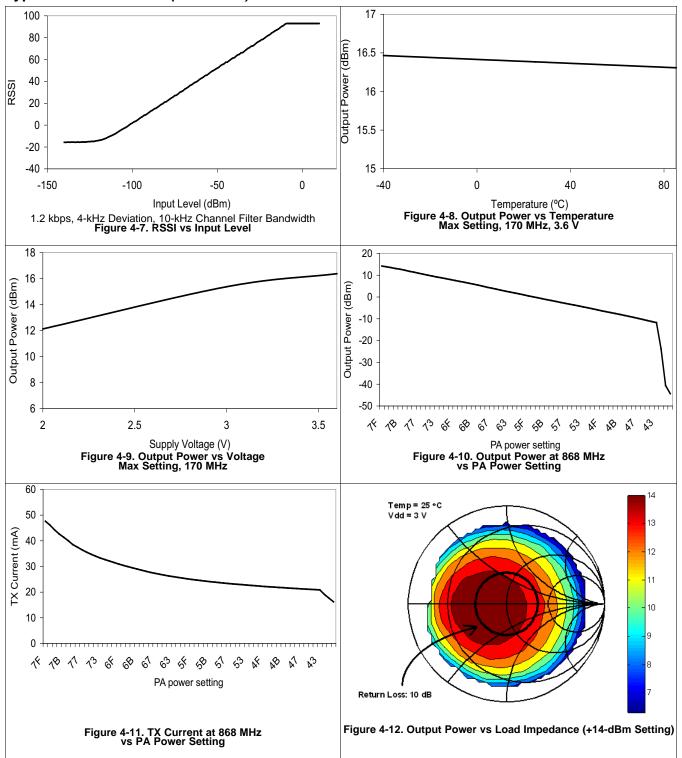
All measurements performed on CC1120EM_868_915 rev.1.0.1, CC1120EM_955 rev.1.2.1, CC1120EM_420_470 rev.1.0.1, or CC1120EM_169 rev.1.2.

Figure 4-12 was measured at the $50-\Omega$ antenna connector.



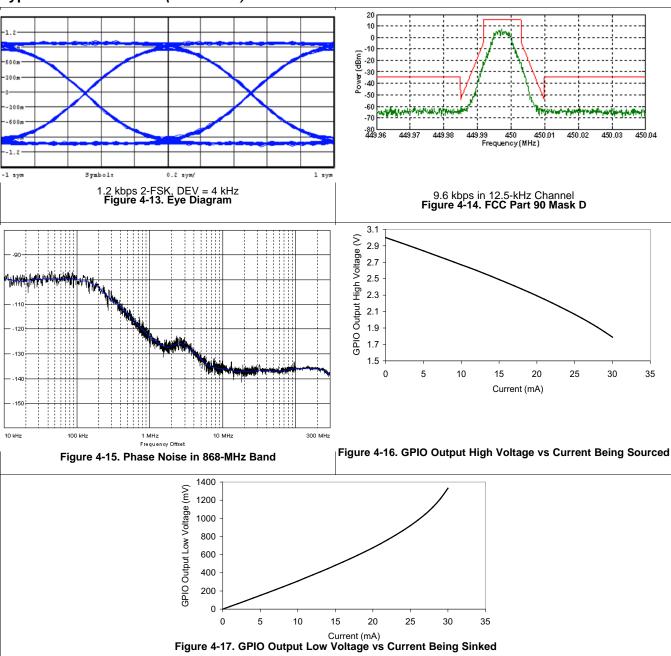


Typical Characteristics (continued)





Typical Characteristics (continued)





5 Detailed Description

5.1 Block Diagram

Figure 5-1 shows the system block diagram of the CC1120 devices.

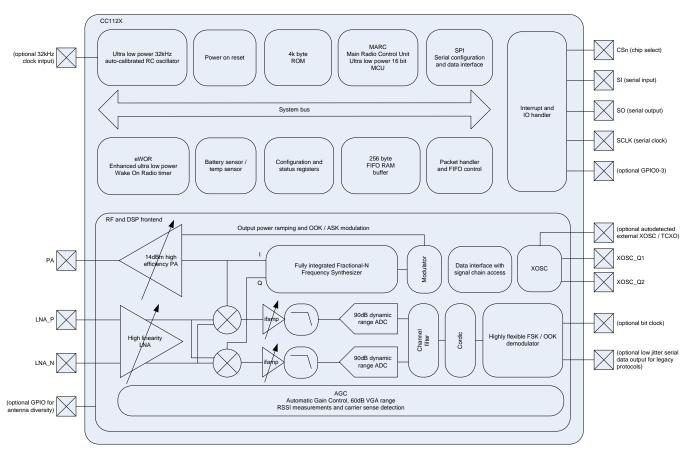


Figure 5-1. System Block Diagram

5.2 Frequency Synthesizer

At the center of the CC1120 device there is a fully integrated, fractional-N, ultra-high-performance frequency synthesizer. The frequency synthesizer is designed for excellent phase noise performance, providing very high selectivity and blocking performance. The system is designed to comply with the most stringent regulatory spectral masks at maximum transmit power.

Either a crystal can be connected to XOSC_Q1 and XOSC_Q2, or a TCXO can be connected to the EXT_XOSC input. The oscillator generates the reference frequency for the synthesizer, as well as clocks for the analog-to-digital converter (ADC) and the digital part. To reduce system cost, CC1120 device has high-accuracy frequency estimation and compensation registers to measure and compensate for crystal inaccuracies. This compensation enables the use of lower cost crystals. If a TCXO is used, the CC1120 device automatically turns on and off the TCXO when needed to support low-power modes and Wake-On-Radio operation.

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5.3 Receiver

The CC1120 device features a highly flexible receiver. The received RF signal is amplified by the low-noise amplifier (LNA) and is down-converted in quadrature (I/Q) to the intermediate frequency (IF). At IF, the I/Q signals are digitized by the high dynamic-range ADCs.

An advanced automatic gain control (AGC) unit adjusts the front-end gain, and enables the CC1120 device to receive strong and weak signals, even in the presence of strong interferers. High-attenuation channels and data filtering enable reception with strong neighbor channel interferers. The I/Q signal is converted to a phase and magnitude signal to support the FSK and OOK modulation schemes.

NOTE

A unique I/Q compensation algorithm removes any problem of I/Q mismatch, thus avoiding time-consuming and costly I/Q image calibration steps.

5.4 Transmitter

The CC1120 transmitter is based on direct synthesis of the RF frequency (in-loop modulation). To use the spectrum effectively, the CC1120 device has extensive data filtering and shaping in TX mode to support high throughput data communication in narrowband channels. The modulator also controls power ramping to remove issues such as spectral splattering when driving external high-power RF amplifiers.

5.5 Radio Control and User Interface

The CC1120 digital control system is built around the main radio control (MARC), which is implemented using an internal high-performance, 16-bit ultra-low-power processor. MARC handles power modes, radio sequencing, and protocol timing.

A 4-wire SPI serial interface is used for configuration and data buffer access. The digital baseband includes support for channel configuration, packet handling, and data buffering. The host MCU can stay in power-down mode until a valid RF packet is received. This greatly reduces power consumption. When the host MCU receives a valid RF packet, it burst-reads the data. This reduces the required computing power.

The CC1120 radio control and user interface are based on the widely used CC1101 transceiver. This relationship enables an easy transition between the two platforms. The command strobes and the main radio states are the same for the two platforms.

For legacy formats, the CC1120 device also supports two serial modes.

- Synchronous serial mode: The CC1120 device performs bit synchronization and provides the MCU with a bit clock with associated data.
- Transparent mode: The CC1120 device outputs the digital baseband signal using a digital interpolation filter to eliminate jitter introduced by digital filtering and demodulation.

5.6 Enhanced Wake-On-Radio (eWOR)

eWOR, using a flexible integrated sleep timer, enables automatic receiver polling with no intervention from the MCU. When the CC1120 device enters RX mode, it listens and then returns to sleep if a valid RF packet is not received. The sleep interval and duty cycle can be configured to make a trade-off between network latency and power consumption. Incoming messages are time-stamped to simplify timer resynchronization.

The eWOR timer runs off an ultra-low-power 32-kHz RC oscillator. To improve timing accuracy, the RC oscillator can be automatically calibrated to the RF crystal in configurable intervals.



5.7 Sniff Mode

The CC1120 device supports quick start up times, and requires few preamble bits. Sniff mode uses these conditions to dramatically reduce the current consumption while the receiver is waiting for data.

Because the CC1120 device can wake up and settle much faster than the duration of most preambles, it is not required to be in RX mode continuously while waiting for a packet to arrive. Instead, the enhanced Wake-On-Radio feature can be used to put the device into sleep mode periodically. By setting an appropriate sleep time, the CC1120 device can wake up and receive the packet when it arrives with no performance loss. This sequence removes the need for accurate timing synchronization between transmitter and receiver, and lets the user trade off current consumption between the transmitter and receiver.

For more information, see the sniff mode design note (SWRA428).

5.8 Antenna Diversity

Antenna diversity can increase performance in a multipath environment. An external antenna switch is required. The CC1201 device uses one of the GPIO pins to automatically control the switch. This device also supports differential output control signals typically used in RF switches.

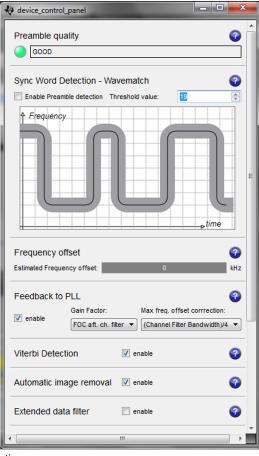
If antenna diversity is enabled, the GPIO alternates between high and low states until a valid RF input signal is detected. An optional acknowledge packet can be transmitted without changing the state of the GPIO.

An incoming RF signal can be validated by received signal strength or by using the automatic preamble detector. Using the automatic preamble detector ensures a more robust system and avoids the need to set a defined signal strength threshold (such a threshold sets the sensitivity limit of the system).

5.9 WaveMatch

Advanced capture logic locks onto the synchronization word and does not require preamble settling bytes. Therefore, receiver settling time is reduced to the settling time of the AGC, typically 4 bits.

The WaveMatch feature also greatly reduces false sync triggering on noise, further reducing the power consumption and improving sensitivity and reliability. The same logic can also be used as a high-performance preamble detector to reliably detect a valid preamble in the channel.



See SWRC046 for more information.

Figure 5-2. Receiver Configurator in SmartRF™ Studio



6 Typical Application Circuit

NOTE

This section is intended only as an introduction.

Very few external components are required for the operation of the CC1120 device. Figure 6-1 shows a typical application circuit. The board layout will greatly influence the RF performance of the CC1120 device. Figure 6-1 does not show decoupling capacitors for power pins.

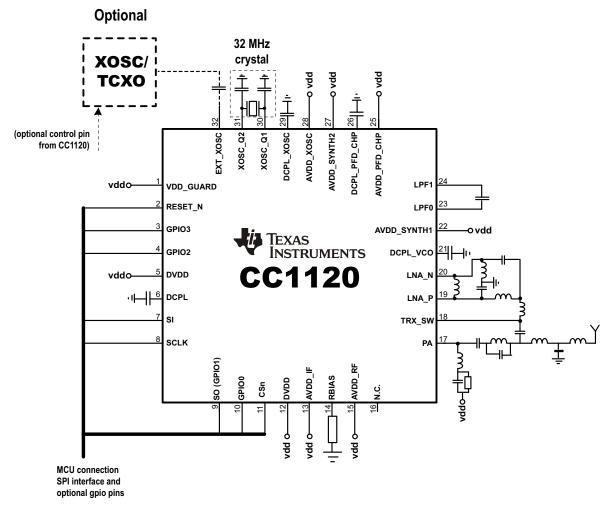


Figure 6-1. Typical Application Circuit

For more information, see the reference designs available for the CC1120 device in Section 7.2, Documentation Support.

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7 Device and Documentation Support

7.1 Device Support

7.1.1 Development Support

7.1.1.1 Configuration Software

The CC1120 device can be configured using the SmartRF Studio software (<u>SWRC046</u>). The SmartRF Studio software is highly recommended for obtaining optimum register settings, and for evaluating performance and functionality.

7.1.2 Device and Development-Support Tool Nomenclature

To designate the stages in the product development cycle, TI assigns prefixes to the part numbers of all microprocessors (MPUs) and support tools. Each device has one of three prefixes: X, P, or null (no prefix) (for example, CC1120). Texas Instruments recommends two of three possible prefix designators for its support tools: TMDX and TMDS. These prefixes represent evolutionary stages of product development from engineering prototypes (TMDX) through fully qualified production devices and tools (TMDS).

Device development evolutionary flow:

X Experimental device that is not necessarily representative of the final device's electrical specifications and may not use production assembly flow.

P Prototype device that is not necessarily the final silicon die and may not necessarily meet final electrical specifications.

null Production version of the silicon die that is fully qualified.

Support tool development evolutionary flow:

TMDX Development-support product that has not yet completed Texas Instruments internal qualification testing.

TMDS Fully qualified development-support product.

X and P devices and TMDX development-support tools are shipped against the following disclaimer:

"Developmental product is intended for internal evaluation purposes."

Production devices and TMDS development-support tools have been characterized fully, and the quality and reliability of the device have been demonstrated fully. Tl's standard warranty applies.

Predictions show that prototype devices (X or P) have a greater failure rate than the standard production devices. Texas Instruments recommends that these devices not be used in any production system because their expected end-use failure rate still is undefined. Only qualified production devices are to be used.

TI device nomenclature also includes a suffix with the device family name. This suffix indicates the package type (for example, RHB) and the temperature range (for example, blank is the default commercial temperature range) provides a legend for reading the complete device name for any CC1120 device.

For orderable part numbers of CC1120 devices in the QFN package types, see the Package Option Addendum of this document, the TI website (www.ti.com), or contact your TI sales representative.



7.2 Documentation Support

The following documents supplement the CC1120 processor. Copies of these documents are available on the Internet at www.ti.com. *Tip:* Enter the literature number in the search box provided at www.ti.com.

CC112x IPC 868- and 915-MHz 2-layer Reference Design **SWRR106 SWRR107** CC112x IPC 868- and 915-MHz 4-layer Reference Design **SWRC220** CC1120EM 169-MHz Reference Design **SWRC221** CC1120EM 420- to 470-MHz Reference Design SWRC222 CC1120EM 868- to 915-MHz Reference Design CC1120EM 955-MHz Reference Design SWRC223 SWRC046 SmartRF Studio Software **SWRA428** CC112x/CC120x Sniff Mode Application Note

7.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

TI Embedded Processors Wiki Texas Instruments Embedded Processors Wiki. Established to help developers get started with Embedded Processors from Texas Instruments and to foster innovation and growth of general knowledge about the hardware and software surrounding these devices.

7.4 Trademarks

SmartRF, E2E are trademarks of Texas Instruments.

7.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

7.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.



8 Mechanical Packaging and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.





9-Nov-2014

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CC1120RHBR	ACTIVE	VQFN	RHB	32	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 85	CC1120	Samples
CC1120RHBT	ACTIVE	VQFN	RHB	32	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 85	CC1120	Samples
CC1120RHMR	OBSOLETE	VQFN	RHM	32		TBD	Call TI	Call TI	-40 to 85	CC1120	
CC1120RHMT	OBSOLETE	VQFN	RHM	32		TBD	Call TI	Call TI	-40 to 85	CC1120	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

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PACKAGE MATERIALS INFORMATION

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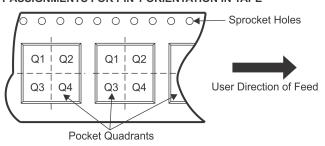
TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CC1120RHBR	VQFN	RHB	32	3000	330.0	12.4	5.3	5.3	1.5	8.0	12.0	Q2
CC1120RHBT	VQFN	RHB	32	250	180.0	12.4	5.3	5.3	1.5	8.0	12.0	Q2

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CC1120RHBR	VQFN	RHB	32	3000	338.1	338.1	20.6
CC1120RHBT	VQFN	RHB	32	250	210.0	185.0	35.0

RHB (S-PVQFN-N32)

PLASTIC QUAD FLATPACK NO-LEAD



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.

- B. This drawing is subject to change without notice.
- C. QFN (Quad Flatpack No-Lead) Package configuration.
- D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- F. Falls within JEDEC MO-220.



RHB (S-PVQFN-N32)

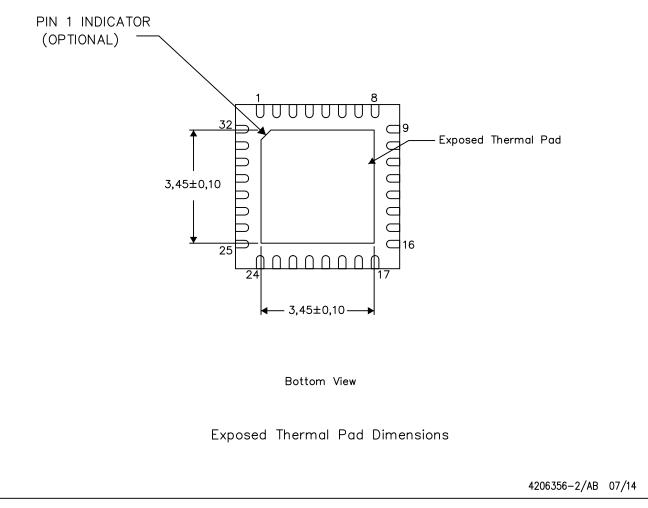
PLASTIC QUAD FLATPACK NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No—Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.

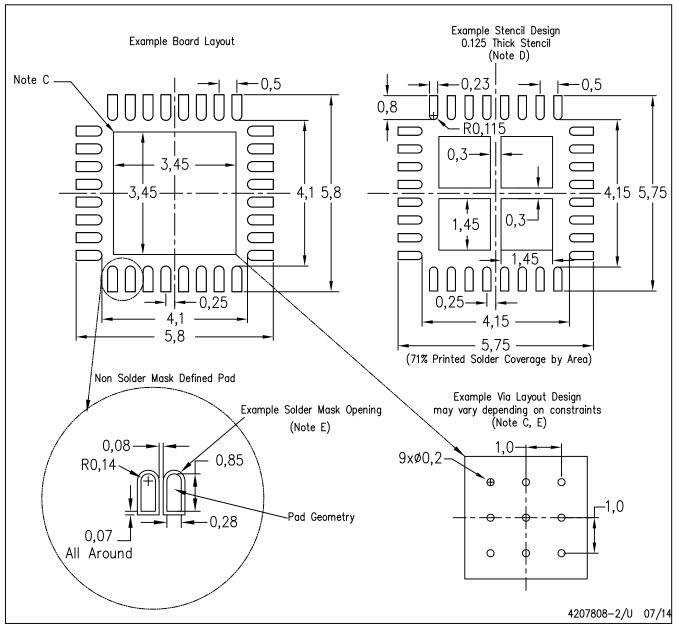


NOTE: A. All linear dimensions are in millimeters



RHB (S-PVQFN-N32)

PLASTIC QUAD FLATPACK NO-LEAD



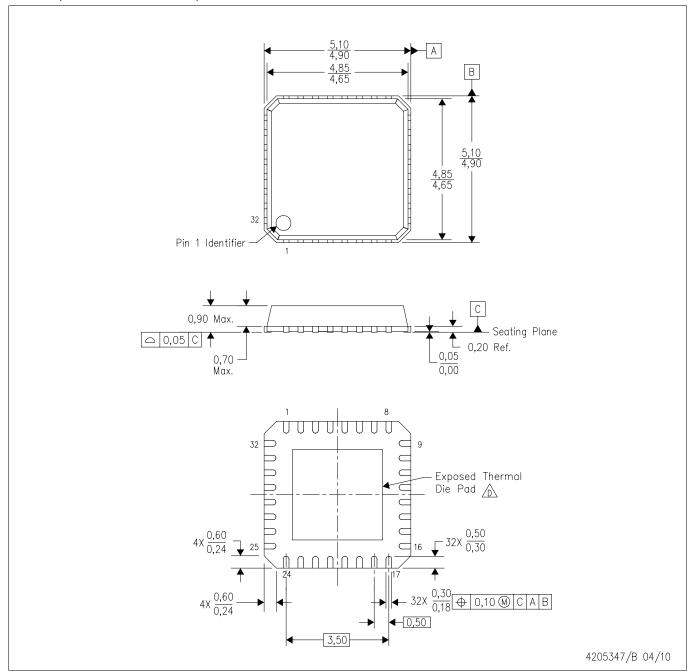
NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat—Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com http://www.ti.com.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- E. Customers should contact their board fabrication site for recommended solder mask tolerances and via tenting recommendations for any larger diameter vias placed in the thermal pad.



RHM (S-PVQFN-N32)

PLASTIC QUAD FLATPACK NO-LEAD



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. QFN (Quad Flatpack No-Lead) Package configuration.
- The package thermal pad must be soldered to the board for thermal and mechanical performance. See the Product Data Sheet for details regarding the exposed thermal pad dimensions.



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